Application/Control Number: 09/945,063

Art Unit: 2878

CLMPTO

01/24/05

1. (Previously Presented) A method of forming multi-layers for manufacturing a thin

film transistor (TFT) using multiple process chambers, comprising:

forming a first layer of silicon dioxide for the thin film transistor on a glass substrate using a first non-chemical physical vapor deposition in a first process chamber;

transferring the substrate including the first layer to a second process chamber without breaking vacuum;

sequentially forming a second layer of amorphous silicon for the thin film transistor in the second process chamber using a second non-chemical physical vapor deposition on the first layer without breaking vacuum for fabricating the thin film transistor; and

forming additional layers on top of the second layer for completing formation of the thin film transistor.

- 2. (Previously Presented) The method of claim 1, wherein the physical vapor deposition for forming the first layer and the second layer comprises pulsed-DC or RF sputtering.
- 3. (Currently Amended) The method of claim 1, wherein the first layer is formed usin gas mixture of Ar+O22 using a SiO22 target P-doped with a resistivity of 1-50 Ohmsecentimeters.
- (Currently Amended) The method of claim 3, wherein the first layer, the second layer and the additional layers form the thin film transistor into a liquid crystal diode display(LCD).

CLAIMS 5-13 (CANCELLED)

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- 14. (Original) The method of claim 1, wherein said forming a first layer is performed by sputtering using a first target comprising silicon dioxide.
- 15. (Original) The method of claim 1, wherein said forming a second layer is performed by sputtering using a target formed of a material selected from the group consisting of single crystalline silicon and polycrystalline silicon.
- 16. (Original) The method of claim 1, wherein the physical vapor deposition for forming the second layer comprises regular-DC, pulsed DC or RF puttering.

CLAIMS 17-40 (CANCELLED)